



Proprietary  
& Confidential C

# 65nm Signoff



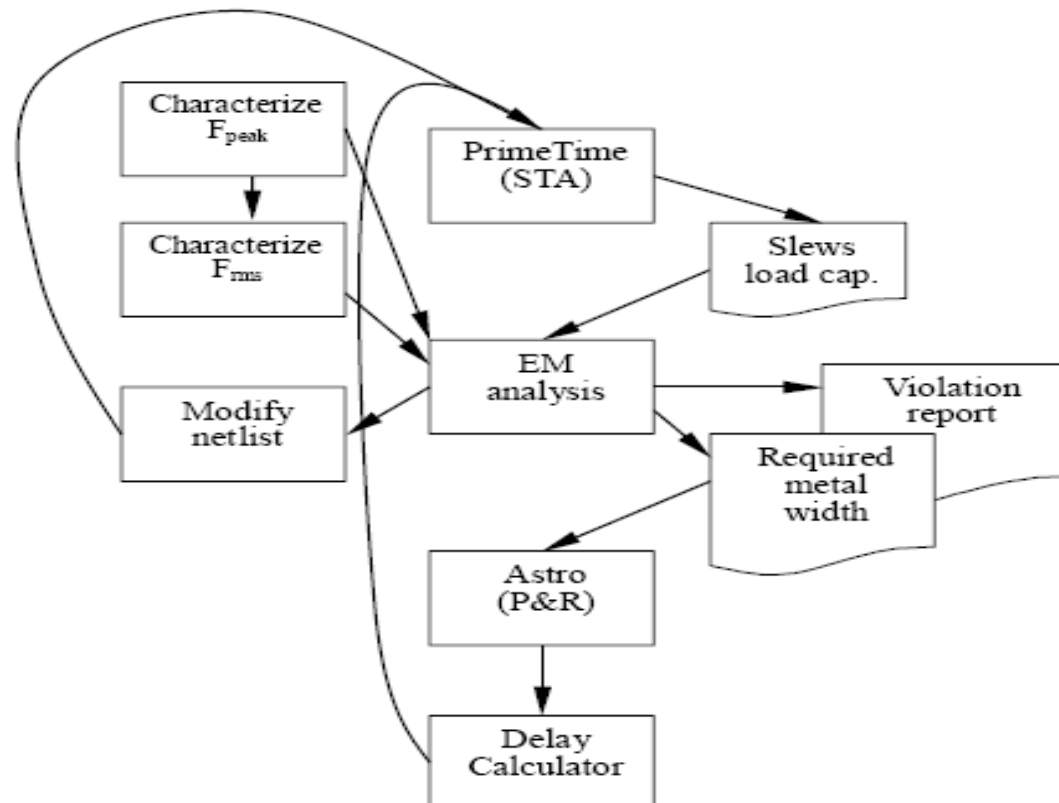
Proprietary  
& Confidential C

# Contents

- **Signal EM Flow**
- **Power Grid Sign-off**
- **Timing Closure & Sign-off**
- **Dummy filling flow & Timing fixing**
- **Others**

# Signal EM Analysis

- Peak/Avg./RMS current
- AstroRail or TSMC utility (Ref. Flow 4.0/5.0)





Proprietary  
& Confidential C

# Signal EM Analysis Procedure

1. The temperature for the signal EM analysis: 125C.
2. The RC corner for the RC extraction: Cworst in 125C.
3. The power consumption is calculated in the LT corner, or the ML corner.
4. Set the reasonable switching activity in the signal EM analysis.



Proprietary  
& Confidential C

# Power Integrity

- **Power grid signed-off in three modes**
  - **Static IR drop**
    - ◆ Average power IR drop  $< 5\% VDD+VSS$  (wire-bond)  $3\%$  ( Flip chip)
  - **Dynamic IR drop**
    - ◆  $4-5X$  Static IR  $< 15\% VDD + VSS$
    - ◆ Dcap insertion
  - **Scan Peak IR around clock-edge  $< 30\% VDD$** 
    - ◆ Peak power usually around clock-edge
    - ◆ Seen many chips failing even in scan-mode
    - ◆ Analyzing IR drop during small timing window when flops are switching
  
- **Power reductions**
  - Leakage: Multi-Vt by default
  - Dynamic: RTL clock gating is highly recommended
  - Comprehensive power approaches for portable device



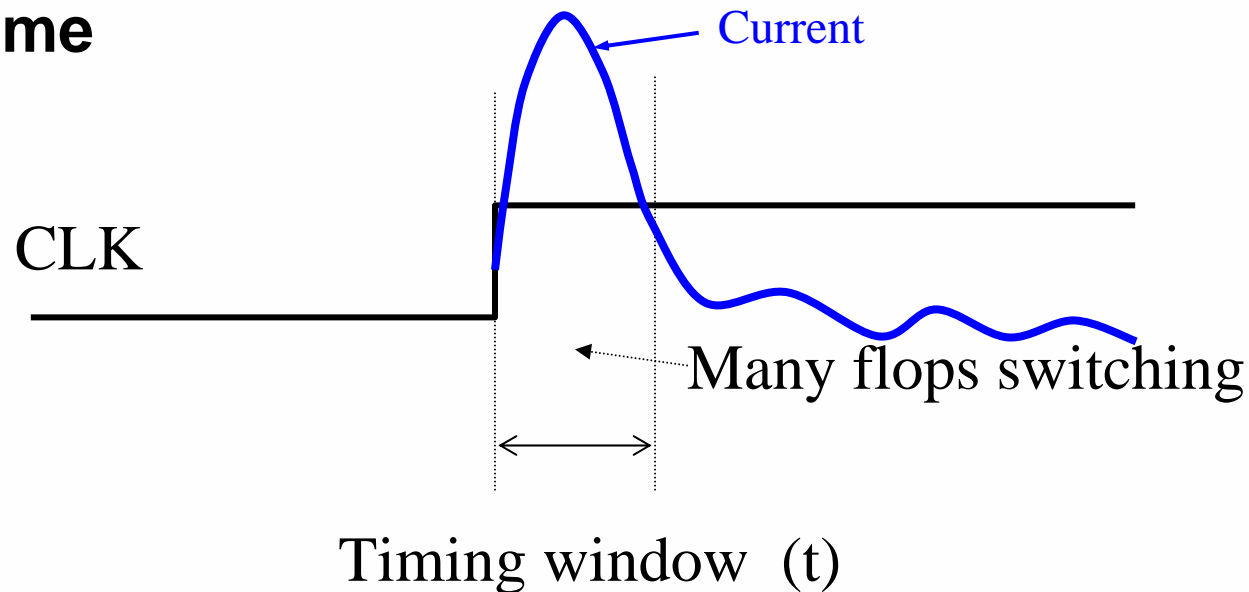
Proprietary  
& Confidential C

# Power Integrity Procedure

1. The temperature for the power EM analysis: 125C.
2. The RC corner for the RC extraction: CWorst in 125C.
3. The power consumption is calculated in the LT corner, -40C/110% VDD/FF, or the ML corner.
4. Set the reasonable toggle rate to calculate the average power consumption.
5. The EM spec is tight in 125C, the current is large in the LT or ML corner, and the power EM criterion in such condition should be most robust.

# Scan Peak Power

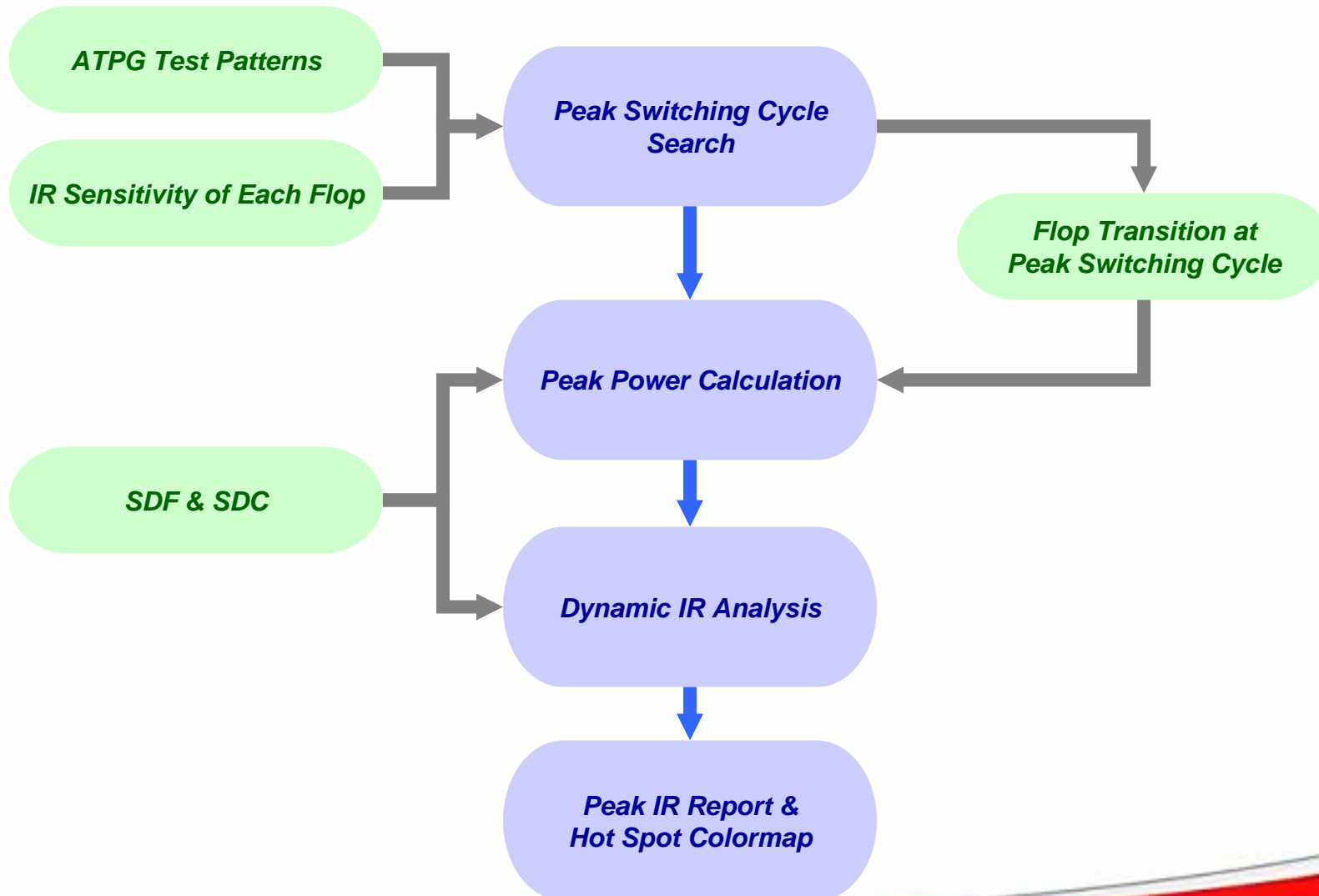
- The most of flops are switching at almost the same time



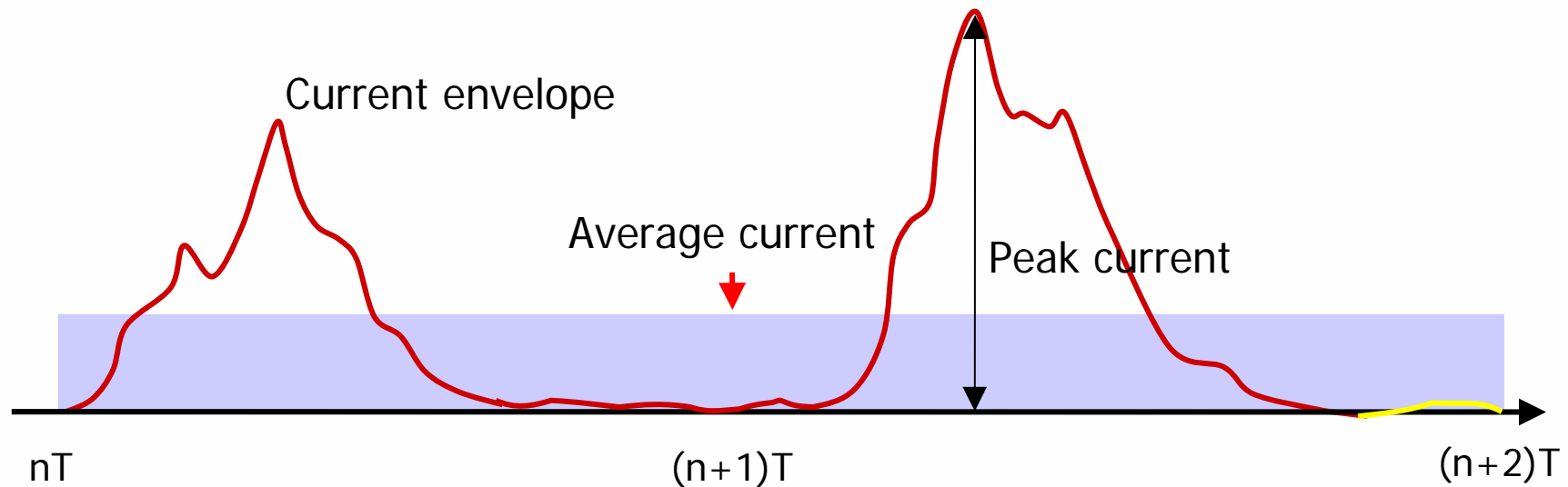
Clock skew + Average CK-Q delay + Average Transition/2



# Scan Power Analysis



# Static vs. Dynamic IR-drop



- Wire sizing can be used to control static IR-drop
- Critical de-cap provides immediate spike filtering

# 65nm PI sign off criteria



Proprietary  
& Confidential C

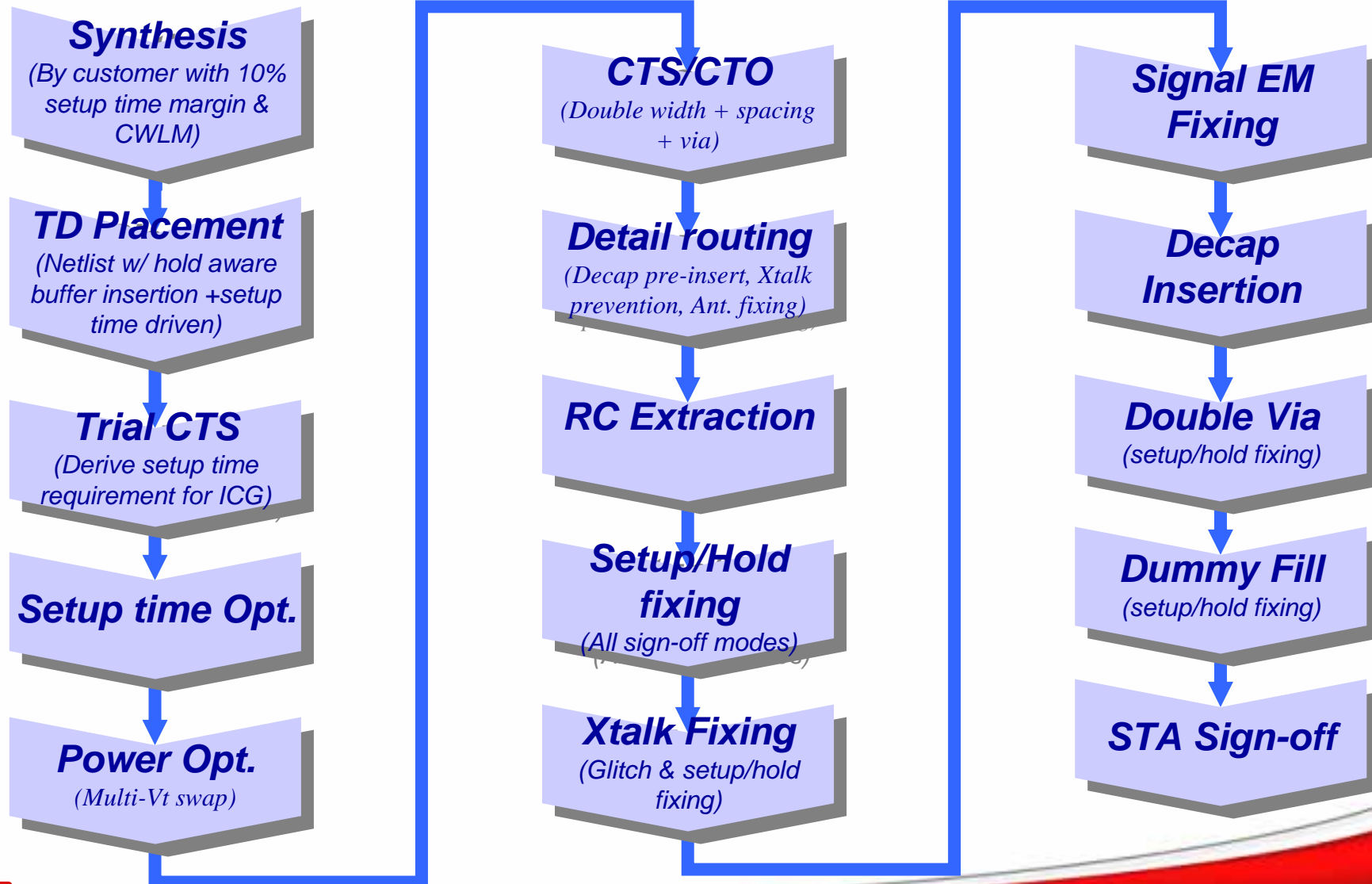
Technology node: 65nm			PI sign off criteria recommended				Corner
			Package				
			Wirebond		Flipchip		
			w/o pkg	w/ pkg	w/o pkg	w/ pkg	
Static			5%	5%	3%	3%	FF/SS VDD: TT
Dynamic	Function	VCD	10%	15-18%	8-10%	13-15%	FF/SS VDD: TT
		Vectorless	10%	15-18%	8-10%	13-15%	FF/SS VDD: TT
	Scan	VCD	10%	15-18%	8-10%	13-15%	FF, TT VDD: TT
		Vectorless	10%	15-18%	15-18%	13-15%	FF, TT VDD: TT

**IR limit : VDD+GND**



Proprietary  
& Confidential C

# Timing Closure





Proprietary  
& Confidential C

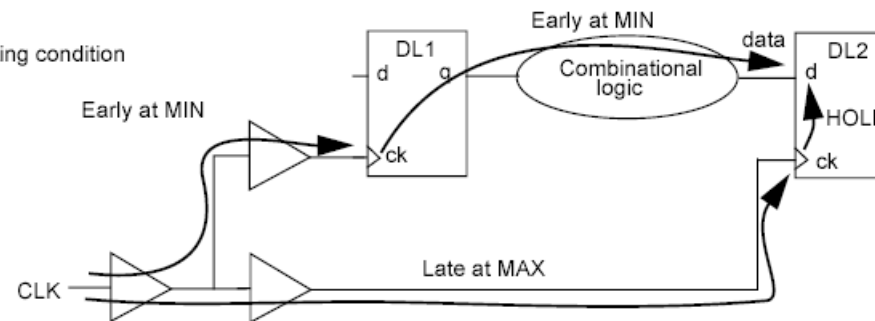
# Timing Sign-off

- **Timing closure taking all kinds of following effects into account**
  - **Multi-mode STA**
  - **Multiple Device & RC Corners**
    - ◆ WC, WCL, BC or LT (-40C)
    - ◆ Cworst, Cbest (RCworst, RCbest, RCtypical)
  - **OCV, Hold margin**
  - **Crosstalk**
  - **DFM – Dummy metals, Dummy Vias**

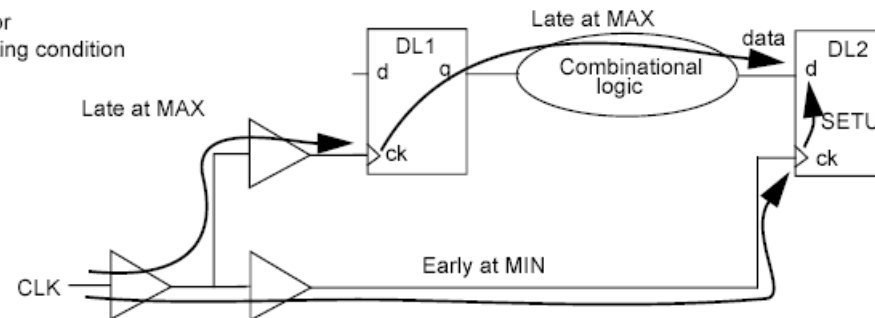
# OCV

## ● OCV – On Chip Variation

Hold check reported for on-chip variation operating condition



Setup check reported for on-chip variation operating condition





Proprietary  
& Confidential C

# Timing Sign-off Recommendation

- Clock jitter is not included

	WC + Cworst	WCL + Cworst	BC or LT + Cbest/Cworst	Max. transition	OCV	Setup margin	Hold margin
65nm	Setup/ hold	Setup/ hold	hold	0.6ns*	WC: 5% BC:10%	0	50ps

\*Max transition applied at WC corner.

\*Over constraint is recommended at APR stage.

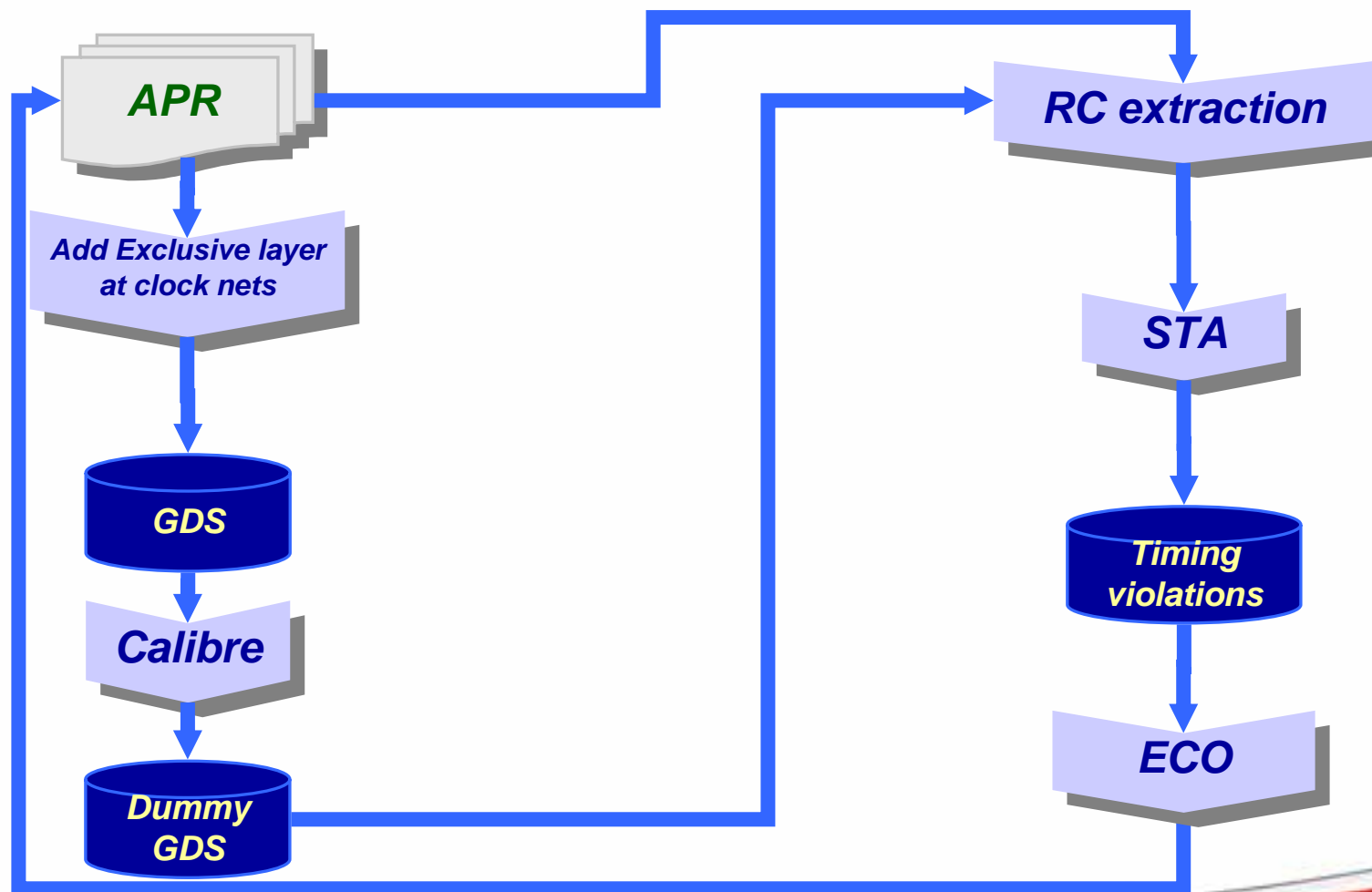
\*\*Typical number showed here:

- OCV and Hold margin design dependant: transition, cell types, IR-drop

\*\*Corner shown here:

- It is the basis. Customer should add more corners based on product application.

# Dummy filling flow & Timing Fixing





Proprietary  
& Confidential C

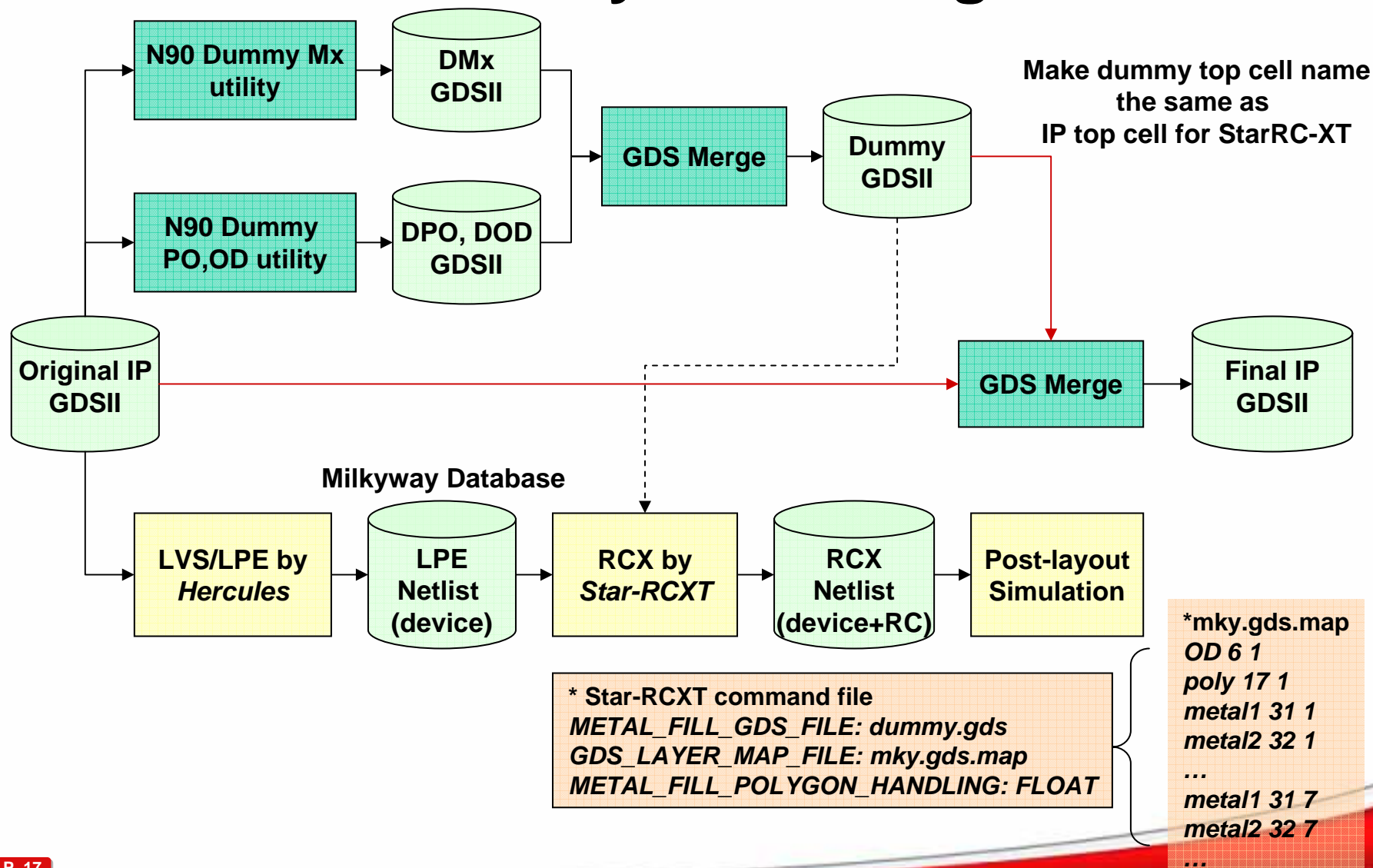
# Dummy Fill Guidelines

- In a cell-based design area, it's recommended to use filler cell with DPO/DOD for empty area (please refer TSMC N90 standard cell library).
- It's recommended to use TSMC fill utility for macro block and chip top level for final GDSII to guarantee global uniformity.
- If using TSMC fill utility for DM and DOD, low densities violations could be waived by TSMC PE. Otherwise, all densities rules should be met.
- Do dummy fill in a bottom-up approach.
  - Macro block meet rules and timing first, then chip level.

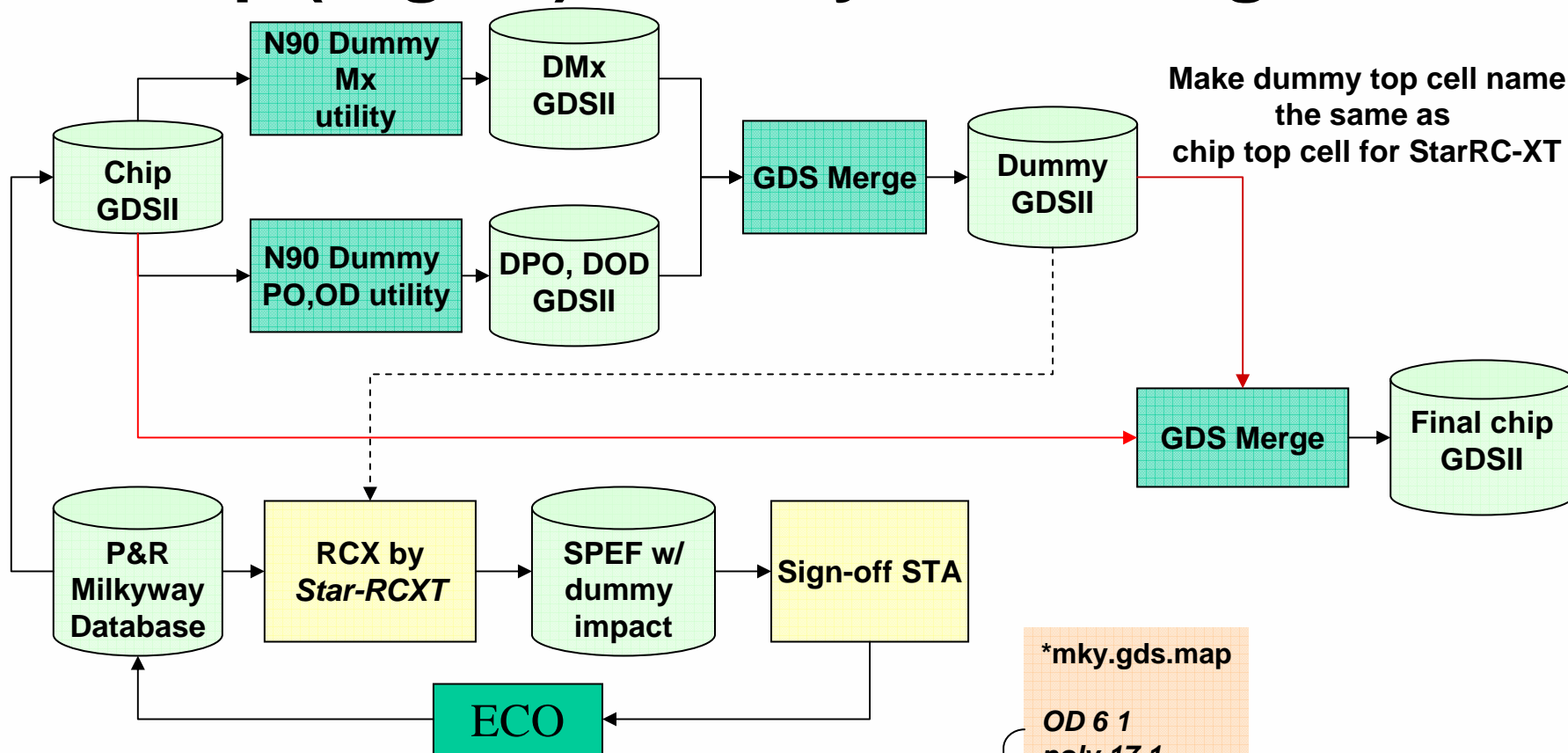


Proprietary & Confidential C

# Macro IP Dummy Fill Timing Flow



# Top (Digital) Dummy Fill Timing Flow

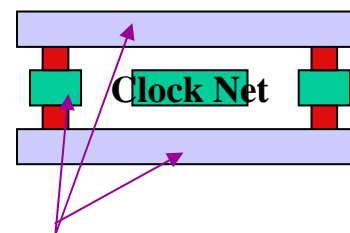
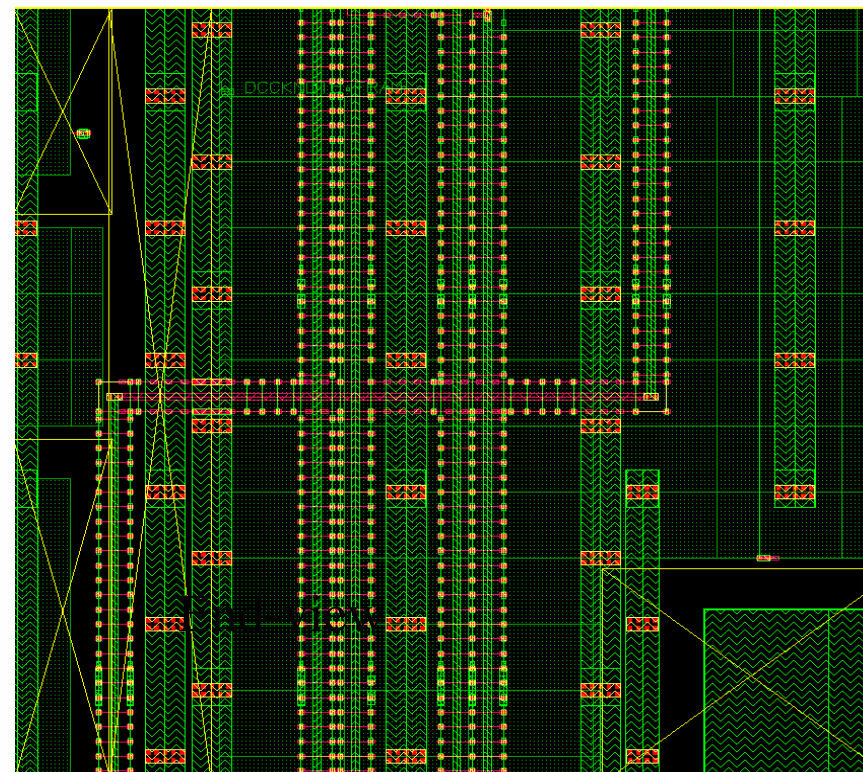
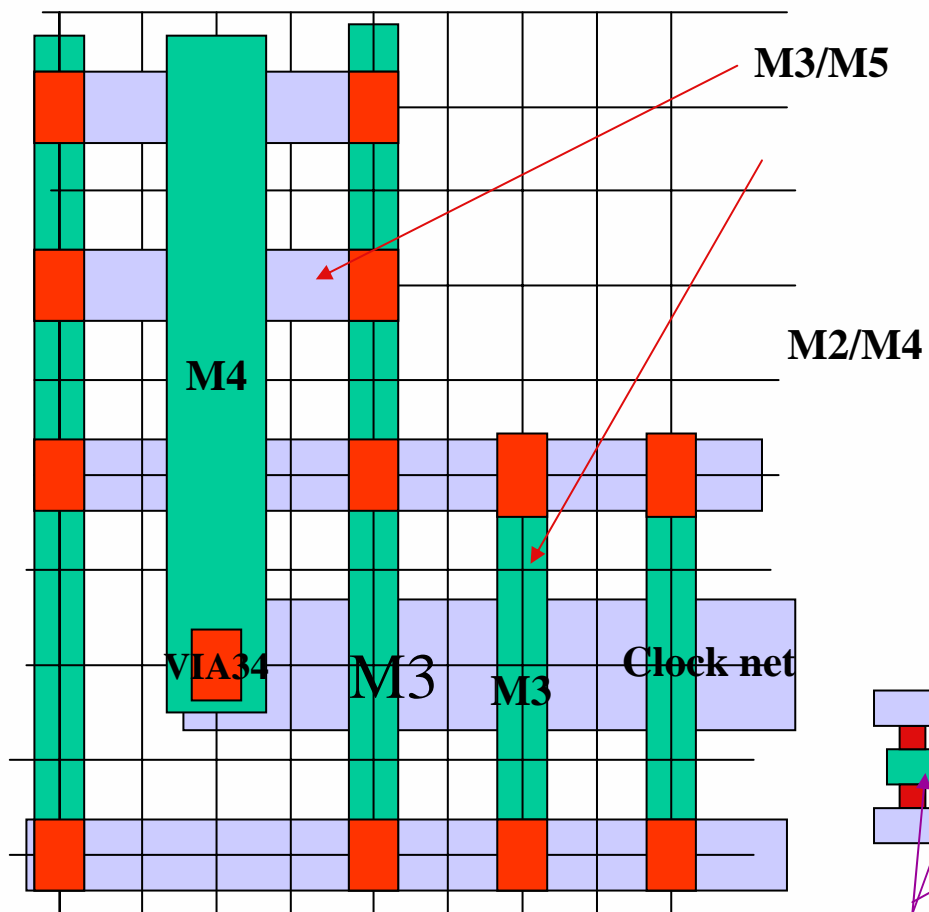


```
* Star-RCXT command file
METAL_FILL_GDS_FILE: dummy.gds
GDS_LAYER_MAP_FILE: mky.gds.map
METAL_FILL_POLYGON_HANDLING: FLOAT
```

```
*mky.gds.map
OD 6 1
poly 17 1
metal1 31 1
metal2 32 1
...
metal1 31 7
metal2 32 7
...
```

# Others: High-Speed Clocks

Top-view



Shielding Net



Proprietary & Confidential C

# Signoff Task vs. EDA Tool

## Task

## EDA Tool

## Major Role

Design tool

<i>ATPG</i>
<i>Floor plan</i>
<i>Placement/CTS/Route</i>
<i>SI</i>
<i>RC extraction</i>

<i>Tmax/fastscan</i>
<i>Astro/SOC encounter</i>
<i>Astro/SOC encounter</i>
<i>Celtic</i>
<i>StarRC</i>

<i>Vector generation/simulation</i>
<i>Floor plan environment</i>
<i>Placement/CTS/Route tool</i>
<i>Xtalk analysis</i>
<i>RC extraction</i>

Signoff

<i>Netlist Handoff</i>
<i>LEC ( Verplex )</i>
<i>Static IR</i>
<i>Dynamic IR</i>
<i>Power EM</i>
<i>Signal EM</i>
<i>STA w/ Incr. SDF</i>
<i>Redundant via insertion</i>
<i>Dummy metal insertion</i>
<i>Antenna</i>
<i>DRC/LVS/ERC</i>

<i>Spyglass &amp; Prime Time</i>
<i>LEC</i>
<i>Voltage Storm</i>
<i>RedHawk</i>
<i>Voltage Storm</i>
<i>Astro/CISD utility</i>
<i>Prime Time</i>
<i>Calibre/Laker/Virtuoso</i>
<i>Calibre/Laker/Virtuoso</i>
<i>Calibre/Hercules</i>
<i>Calibre/Hercules</i>

<i>Sanity Check</i>
<i>formal validation</i>
<i>Static IR drop analysis</i>
<i>Dynamic IR drop analysis</i>
<i>Power Ring reliability issue</i>
<i>Signal wire reliability issue</i>
<i>Static timing analysis</i>
<i>Yield improvement</i>
<i>Yield improvement</i>
<i>Antenna effect check</i>
<i>TSMC design rule checks</i>